Intel - EPF10K70RC240-3GZ Datasheet

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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	468
Number of Logic Elements/Cells	3744
Total RAM Bits	18432
Number of I/O	189
Number of Gates	118000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP Exposed Pad
Supplier Device Package	240-RQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k70rc240-3gz

Notes to tables:
(1) FLEX 10K and FLEX 10KA device package types include plastic J-lead chip carrier (PLCC), thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), ball-grid array (BGA), pin-grid array (PGA), and FineLine BGA™ packages.
(2) This option is supported with a 256-pin FineLine BGA package. By using SameFrame pin migration, all FineLine BGA packages are pin compatible. For example, a board can be designed to support both 256-pin and 484-pin FineLine BGA packages. The Altera software automatically avoids conflicting pins when future migration is set.

General Description

Altera's FLEX 10K devices are the industry's first embedded PLDs. Based on reconfigurable CMOS SRAM elements, the Flexible Logic Element MatriX (FLEX) architecture incorporates all features necessary to implement common gate array megafunctions. With up to 250,000 gates, the FLEX 10K family provides the density, speed, and features to integrate entire systems, including multiple 32-bit buses, into a single device.

FLEX 10K devices are reconfigurable, which allows 100% testing prior to shipment. As a result, the designer is not required to generate test vectors for fault coverage purposes. Additionally, the designer does not need to manage inventories of different ASIC designs; FLEX 10K devices can be configured on the board for the specific functionality required.

Table 6 shows FLEX 10K performance for some common designs. All performance values were obtained with Synopsys DesignWare or LPM functions. No special design technique was required to implement the applications; the designer simply inferred or instantiated a function in a Verilog HDL, VHDL, Altera Hardware Description Language (AHDL), or schematic design file.

Table 6. FLEX 10K & FLEX 10KA Performance

Application	Resources Used		Performance				Units
	LEs	EABs	-1 Speed Grade	-2 Speed Grade	-3 Speed Grade	-4 Speed Grade	
16-bit loadable counter *(1)*	16	0	204	166	125	95	MHz
16-bit accumulator *(1)*	16	0	204	166	125	95	MHz
16-to-1 multiplexer *(2)*	10	0	4.2	5.8	6.0	7.0	ns
256 × 8 RAM read cycle speed *(3)*	0	1	172	145	108	84	MHz
256 × 8 RAM write cycle speed *(3)*	0	1	106	89	68	63	MHz

Notes:
(1) The speed grade of this application is limited because of clock high and low specifications.
(2) This application uses combinatorial inputs and outputs.
(3) This application uses registered inputs and outputs.

LE Operating Modes

The FLEX 10K LE can operate in the following four modes:

- Normal mode
- Arithmetic mode
- Up/down counter mode
- Clearable counter mode

Each of these modes uses LE resources differently. In each mode, seven available inputs to the LE—the four data inputs from the LAB local interconnect, the feedback from the programmable register, and the carry-in and cascade-in from the previous LE—are directed to different destinations to implement the desired logic function. Three inputs to the LE provide clock, clear, and preset control for the register. The Altera software, in conjunction with parameterized functions such as LPM and DesignWare functions, automatically chooses the appropriate mode for common functions such as counters, adders, and multipliers. If required, the designer can also create special-purpose functions which use a specific LE operating mode for optimal performance.

The architecture provides a synchronous clock enable to the register in all four modes. The Altera software can set `DATA1` to enable the register synchronously, providing easy implementation of fully synchronous designs.

Figure 9 shows the LE operating modes.

Normal Mode

The normal mode is suitable for general logic applications and wide decoding functions that can take advantage of a cascade chain. In normal mode, four data inputs from the LAB local interconnect and the carry-in are inputs to a four-input LUT. The Compiler automatically selects the carry-in or the DATA3 signal as one of the inputs to the LUT. The LUT output can be combined with the cascade-in signal to form a cascade chain through the cascade-out signal. Either the register or the LUT can be used to drive both the local interconnect and the FastTrack Interconnect at the same time.

The LUT and the register in the LE can be used independently; this feature is known as register packing. To support register packing, the LE has two outputs; one drives the local interconnect and the other drives the FastTrack Interconnect. The DATA4 signal can drive the register directly, allowing the LUT to compute a function that is independent of the registered signal; a three-input function can be computed in the LUT, and a fourth independent signal can be registered. Alternatively, a four-input function can be generated, and one of the inputs to this function can be used to drive the register. The register in a packed LE can still use the clock enable, clear, and preset signals in the LE. In a packed LE, the register can drive the FastTrack Interconnect while the LUT drives the local interconnect, or vice versa.

Arithmetic Mode

The arithmetic mode offers 2 three-input LUTs that are ideal for implementing adders, accumulators, and comparators. One LUT computes a three-input function, and the other generates a carry output. As shown in Figure 9 on page 19, the first LUT uses the carry-in signal and two data inputs from the LAB local interconnect to generate a combinatorial or registered output. For example, in an adder, this output is the sum of three signals: a, b, and carry-in. The second LUT uses the same three signals to generate a carry-out signal, thereby creating a carry chain. The arithmetic mode also supports simultaneous use of the cascade chain.

During compilation, the Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset

In addition to the six clear and preset modes, FLEX 10K devices provide a chip-wide reset pin that can reset all registers in the device. Use of this feature is set during design entry. In any of the clear and preset modes, the chip-wide reset overrides all other signals. Registers with asynchronous presets may be preset when the chip-wide reset is asserted. Inversion can be used to implement the asynchronous preset. Figure 10 shows examples of how to enter a section of a design for the desired functionality.

Slew-Rate Control

The output buffer in each IOE has an adjustable output slew rate that can be configured for low-noise or high-speed performance. A slower slew rate reduces system noise and adds a maximum delay of approximately 2.9 ns. The fast slew rate should be used for speed-critical outputs in systems that are adequately protected against noise. Designers can specify the slew rate on a pin-by-pin basis during design entry or assign a default slew rate to all pins on a device-wide basis. The slow slew rate setting affects only the falling edge of the output.

Open-Drain Output Option

FLEX 10K devices provide an optional open-drain (electrically equivalent to an open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write enable signals) that can be asserted by any of several devices. It can also provide an additional wired-OR plane. Additionally, the Altera software can convert tri-state buffers with grounded data inputs to open-drain pins automatically.

Open-drain output pins on FLEX 10K devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the open-drain pin is active, it will drive low. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Output pins on 5.0-V FLEX 10K devices with V_{CCIO} = 3.3 V or 5.0 V (with a pull-up resistor to the 5.0-V supply) can also drive 5.0-V CMOS input pins. In this case, the pull-up transistor will turn off when the pin voltage exceeds 3.3 V. Therefore, the pin does not have to be open-drain.

MultiVolt I/O Interface

The FLEX 10K device architecture supports the MultiVolt I/O interface feature, which allows FLEX 10K devices to interface with systems of differing supply voltages. These devices have one set of V_{CC} pins for internal operation and input buffers (VCCINT) and another set for I/O output drivers (VCCIO).

Table 12 describes the FLEX 10K device supply voltages and MultiVolt I/O support levels.

Table 12. Supply Voltages & MultiVolt I/O Support Levels

Devices	Supply Voltage (V)		MultiVolt I/O Support Levels (V)	
	V_{CCINT}	V_{CCIO}	Input	Output
FLEX 10K *(1)*	5.0	5.0	3.3 or 5.0	5.0
	5.0	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K50V *(1)*	3.3	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K130V	3.3	3.3	3.3 or 5.0	3.3 or 5.0
FLEX 10KA *(1)*	3.3	3.3	2.5, 3.3, or 5.0	3.3 or 5.0
	3.3	2.5	2.5, 3.3, or 5.0	2.5

Note
(1) 240-pin QFP packages do not support the MultiVolt I/O features, so they do not have separate V_{CCIO} pins.

Power Sequencing & Hot-Socketing

Because FLEX 10K devices can be used in a multi-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The V_{CCIO} and V_{CCINT} power supplies can be powered in any order.

Signals can be driven into FLEX 10KA devices before and during power up without damaging the device. Additionally, FLEX 10KA devices do not drive out during power up. Once operating conditions are reached, FLEX 10KA devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10K devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. All FLEX 10K devices can also be configured using the JTAG pins through the BitBlaster serial download cable, or ByteBlasterMV parallel port download cable, or via hardware that uses the Jam™ programming and test language. JTAG BST can be performed before or after configuration, but not during configuration. FLEX 10K devices support the JTAG instructions shown in Table 13.

Table 18. FLEX 10K 5.0-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
V_{CCIO}	Supply voltage for output buffers, 5.0-V operation	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage		–0.5	V_{CCINT} + 0.5	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 35. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.

(2) Operating conditions: V_{CCIO} = 5.0 V ± 5% for commercial use in FLEX 10K devices.
V_{CCIO} = 5.0 V ± 10% for industrial use in FLEX 10K devices.
V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10KA devices.

(3) Operating conditions: V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10K devices.
V_{CCIO} = 2.5 V ± 0.2 V for commercial or industrial use in FLEX 10KA devices.

(4) Operating conditions: V_{CCIO} = 2.5 V, 3.3 V, or 5.0 V.

(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.

(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.

(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

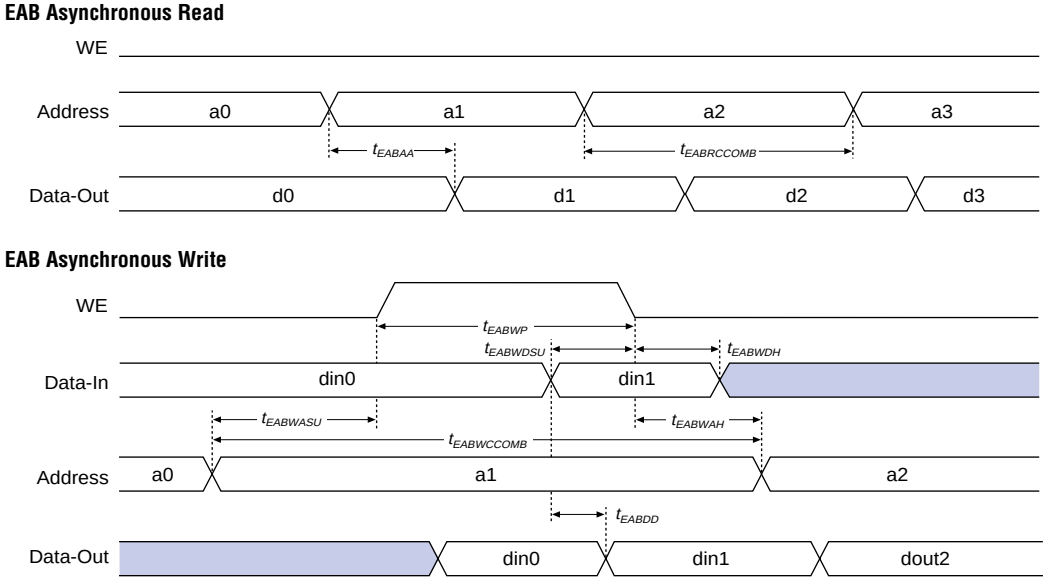
(8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.

(9) Contact Altera Applications for test circuit specifications and test conditions.

(10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms



Tables 39 through 47 show EPF10K10 and EPF10K20 device internal and external timing parameters.

Table 39. EPF10K10 & EPF10K20 Device LE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{LUT}		1.4		1.7	ns
t_{CLUT}		0.6		0.7	ns
t_{RLUT}		1.5		1.9	ns
t_{PACKED}		0.6		0.9	ns
t_{EN}		1.0		1.2	ns
t_{CICO}		0.2		0.3	ns
t_{CGEN}		0.9		1.2	ns
t_{CGENR}		0.9		1.2	ns
t_{CASC}		0.8		0.9	ns
t_{C}		1.3		1.5	ns
t_{CO}		0.9		1.1	ns
t_{COMB}		0.5		0.6	ns
t_{SU}	1.3		2.5		ns
t_{H}	1.4		1.6		ns
t_{PRE}		1.0		1.2	ns
t_{CLR}		1.0		1.2	ns
t_{CH}	4.0		4.0		ns
t_{CL}	4.0		4.0		ns

Table 50. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.9	ns
$t_{EABDATA2}$		4.8		6.0	ns
t_{EABWE1}		1.0		1.2	ns
t_{EABWE2}		5.0		6.2	ns
t_{EABCLK}		1.0		2.2	ns
t_{EABCO}		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.9	ns
t_{EABSU}	1.5		1.8		ns
t_{EABH}	2.0		2.5		ns
t_{AA}		8.7		10.7	ns
t_{WP}	5.8		7.2		ns
t_{WDSU}	1.6		2.0		ns
t_{WDH}	0.3		0.4		ns
t_{WASU}	0.5		0.6		ns
t_{WAH}	1.0		1.2		ns
t_{WO}		5.0		6.2	ns
t_{DD}		5.0		6.2	ns
t_{EABOUT}		0.5		0.6	ns
t_{EABCH}	4.0		4.0		ns
t_{EABCL}	5.8		7.2		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 57 through 63 show EPF10K70 device internal and external timing parameters.

Table 57. EPF10K70 Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.5		1.6		2.0	ns
t_{PACKED}		0.8		0.9		1.3	ns
t_{EN}		0.8		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.0		1.1		1.4	ns
t_{CGENR}		1.1		1.2		1.5	ns
t_{CASC}		1.0		1.1		1.3	ns
t_{C}		0.7		0.8		1.0	ns
t_{CO}		0.9		1.0		1.4	ns
t_{COMB}		0.4		0.5		0.7	ns
t_{SU}	1.9		2.1		2.6		ns
t_{H}	2.1		2.3		3.1		ns
t_{PRE}		0.9		1.0		1.4	ns
t_{CLR}		0.9		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 58. EPF10K70 Device IOE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		0.0		0.0		0.0	ns
t_{IOC}		0.4		0.5		0.7	ns
t_{IOCO}		0.4		0.4		0.9	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	4.5		5.0		6.2		ns
t_{IOH}	0.4		0.5		0.7		ns
t_{IOCLR}		0.6		0.7		1.6	ns
t_{OD1}		3.6		4.0		5.0	ns
t_{OD2}		5.6		6.3		7.3	ns
t_{OD3}		6.9		7.7		8.7	ns
t_{XZ}		5.5		6.2		6.8	ns
t_{ZX1}		5.5		6.2		6.8	ns
t_{ZX2}		7.5		8.5		9.1	ns
t_{ZX3}		8.8		9.9		10.5	ns
t_{INREG}		8.0		9.0		10.2	ns
t_{IOFD}		7.2		8.1		10.3	ns
t_{INCOMB}		7.2		8.1		10.3	ns

Table 60. EPF10K70 Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		12.1		13.7		17.0	ns
$t_{EABRCCOMB}$	12.1		13.7		17.0		ns
$t_{EABRCREG}$	8.6		9.7		11.9		ns
t_{EABWP}	5.2		5.8		7.2		ns
$t_{EABWCCOMB}$	6.5		7.3		9.0		ns
$t_{EABWCREG}$	11.6		13.0		16.0		ns
t_{EABDD}		8.8		10.0		12.5	ns
$t_{EABDATACO}$		1.7		2.0		3.4	ns
$t_{EABDATASU}$	4.7		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.9		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.8		2.1		2.7		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	4.1		4.7		5.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		8.4		9.5		11.8	ns

Table 66. EPF10K100 Device EAB Internal Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.5		1.9	ns
$t_{EABDATA2}$		4.8		4.8		6.0	ns
t_{EABWE1}		1.0		1.0		1.2	ns
t_{EABWE2}		5.0		5.0		6.2	ns
t_{EABCLK}		1.0		1.0		2.2	ns
t_{EABCO}		0.5		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.5		1.9	ns
t_{EABSU}	1.5		1.5		1.8		ns
t_{EABH}	2.0		2.0		2.5		ns
t_{AA}		8.7		8.7		10.7	ns
t_{WP}	5.8		5.8		7.2		ns
t_{WDSU}	1.6		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.5		0.5		0.6		ns
t_{WAH}	1.0		1.0		1.2		ns
t_{WO}		5.0		5.0		6.2	ns
t_{DD}		5.0		5.0		6.2	ns
t_{EABOUT}		0.5		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.8		5.8		7.2		ns

Table 75. EPF10K50V Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.7		6.0		7.1		8.2	ns
t_{DIN2LE}		2.5		2.6		3.1		3.9	ns
$t_{DIN2DATA}$		4.4		5.9		6.8		7.7	ns
$t_{DCLK2IOE}$		2.5		3.9		4.7		5.5	ns
$t_{DCLK2LE}$		2.5		2.6		3.1		3.9	ns
$t_{SAMELAB}$		0.2		0.2		0.3		0.3	ns
$t_{SAMEROW}$		2.8		3.0		3.2		3.4	ns
$t_{SAMECOLUMN}$		3.0		3.2		3.4		3.6	ns
$t_{DIFFROW}$		5.8		6.2		6.6		7.0	ns
$t_{TWOROWS}$		8.6		9.2		9.8		10.4	ns
$t_{LEPERIPH}$		4.5		5.5		6.1		7.0	ns
$t_{LABCARRY}$		0.3		0.4		0.5		0.7	ns
$t_{LABCASC}$		0.0		1.3		1.6		2.0	ns

Table 76. EPF10K50V Device External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.2		14.0		17.2		21.1	ns
t_{INSU} *(2), (3)*	5.5		4.2		5.2		6.9		ns
t_{INH} *(3)*	0.0		0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns

Table 77. EPF10K50V Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.0		2.8		3.5		4.1		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns
$t_{XZBIDIR}$		8.0		9.8		11.8		14.3	ns
$t_{ZXBIDIR}$		8.0		9.8		11.8		14.3	ns

Table 96. EPF10K30A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.9		4.4		5.1	ns
t_{DIN2LE}		1.2		1.5		1.9	ns
$t_{DIN2DATA}$		3.2		3.6		4.5	ns
$t_{DCLK2IOE}$		3.0		3.5		4.6	ns
$t_{DCLK2LE}$		1.2		1.5		1.9	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.4		2.7	ns
$t_{SAMECOLUMN}$		1.3		1.4		1.9	ns
$t_{DIFFROW}$		3.6		3.8		4.6	ns
$t_{TWOROWS}$		5.9		6.2		7.3	ns
$t_{LEPERIPH}$		3.5		3.8		4.1	ns
$t_{LABCARRY}$		0.3		0.4		0.5	ns
$t_{LABCASC}$		0.9		1.1		1.4	ns

Table 97. EPF10K30A External Reference Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.0		13.0		17.0	ns
t_{INSU} *(2)*, *(3)*	2.5		3.1		3.9		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.4	2.0	6.2	2.0	8.3	ns

Table 98. EPF10K30A Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.2		4.9		6.8		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.4	2.0	6.2	2.0	8.3	ns
$t_{XZBIDIR}$		6.2		7.5		9.8	ns
$t_{ZXBIDIR}$		6.2		7.5		9.8	ns

Table 102. EPF10K100A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.8		7.8		9.2	ns
$t_{EABRCCOMB}$	6.8		7.8		9.2		ns
$t_{EABRCREG}$	5.4		6.2		7.4		ns
t_{EABWP}	3.2		3.7		4.4		ns
$t_{EABWCCOMB}$	3.4		3.9		4.7		ns
$t_{EABWCREG}$	9.4		10.8		12.8		ns
t_{EABDD}		6.1		6.9		8.2	ns
$t_{EABDATACO}$		2.1		2.3		2.9	ns
$t_{EABDATASU}$	3.7		4.3		5.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	2.8		3.3		3.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.4		4.0		4.6		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.9		2.3		2.6		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		5.1		5.7		6.9	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 37 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. Figure 31 illustrates the incoming and generated clock specifications.

Figure 31. Specifications for the Incoming & Generated Clocks

The t_I parameter refers to the nominal input clock period; the t_O parameter refers to the nominal output clock period.

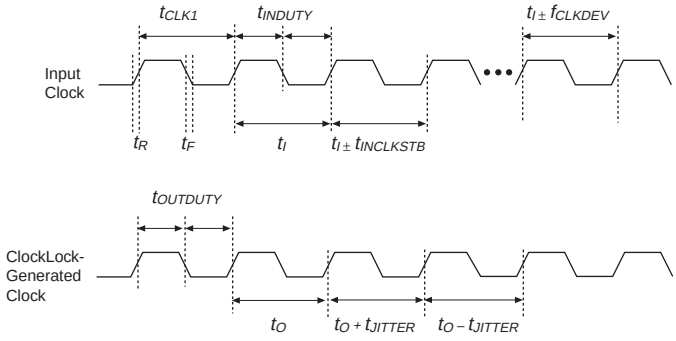


Table 113 summarizes the ClockLock and ClockBoost parameters.

Table 113. ClockLock & ClockBoost Parameters (Part 1 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
t_R	Input rise time			2	ns
t_F	Input fall time			2	ns
t_{INDUTY}	Input duty cycle	45		55	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)	30		80	MHz
t_{CLK1}	Input clock period (ClockBoost clock multiplication factor equals 1)	12.5		33.3	ns
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16		50	MHz
t_{CLK2}	Input clock period (ClockBoost clock multiplication factor equals 2)	20		62.5	ns

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 3)

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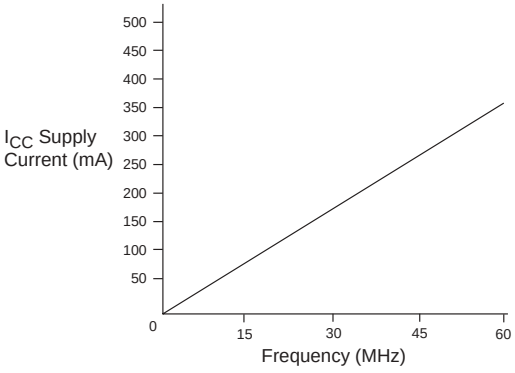
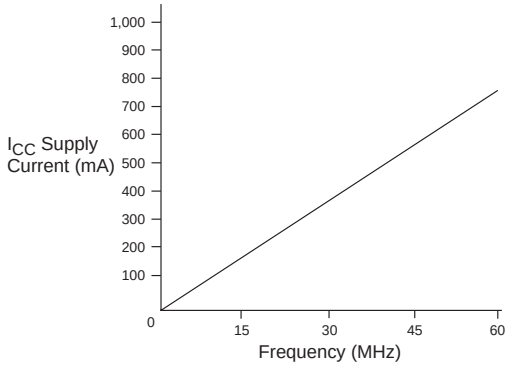
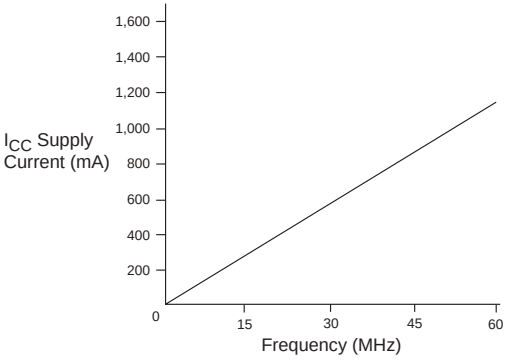


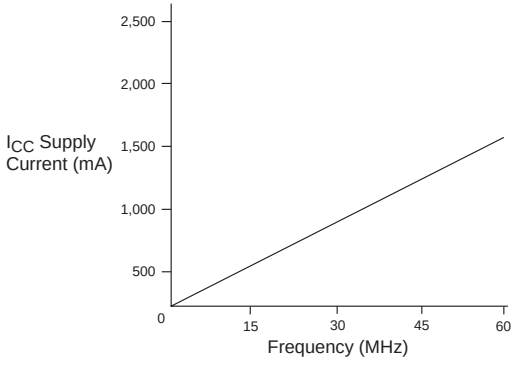
EPF10K20



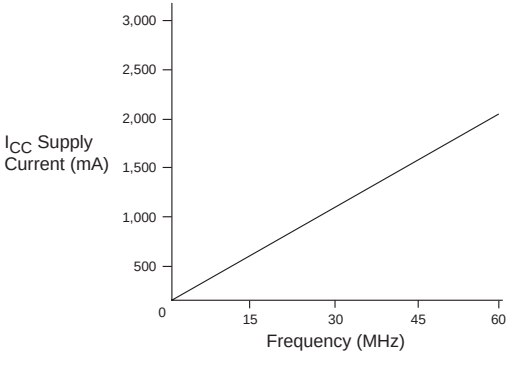
EPF10K30



EPF10K40



EPF10K50



EPF10K70